



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

10/B
w/ Drawing
Attach. 3-18-03
Mullish

In re Application

Inventor(s): Krivokapic, et al.

SC/Serial No.: 09/711,445

Confirm. No.: 7218

Filed: November 13, 2000

Title: SELF-ALIGNED TRIPLE GATE SILICON-ON-
INSULATOR (SOI) DEVICE

PATENT APPLICATION

Art Unit: 2811

Examiner: Owens, Douglas W.

Customer No. 23910

CERTIFICATE OF MAILING UNDER 37 C.F.R. § 1.8

I hereby certify that this correspondence is being deposited in the United States Postal Service with sufficient postage as first class mail in an envelope addressed to Commissioner for Patents, Washington, DC 20231, on March 3, 2003.


(Attorney Signature)

Stephen R. Bachmann, Reg. No. 50,806

Signature Date: March 3, 2003

RESPONSE C TO OFFICE ACTION UNDER 37 C.F.R. § 1.111

Commissioner for Patents
Washington, DC 20231

Sir:

This RESPONSE C is in reply to the Office action mailed December 3, 2002. An appropriate Petition for Extension of Time to Respond is submitted herewith, together with the appropriate fee.

Amendments

All amendments made herein comply with the format proposed by the revision to 37 CFR

1.121 (Manner of Making Amendments). Please amend the above-identified application as follows:

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In the Title:

✓ Please replace the title with the new title shown below:

METHOD OF MAKING A DUAL GATE TRANSISTOR

In the Drawings:

Enclosed are formal drawing replacement sheets for Figs. 1, 4B, 5B, 13A, 14A-C, 15A-C, and 16A, which include Applicant's desired changes, without markings, and comply with § 1.84. Subject to the approval of the Examiner, it is respectfully requested that the new drawing sheets be substituted for the originally filed drawing sheets for Figs. 1, 4B, 5B, 13A, 14A-C, 15A-C, and 16A. The changes are explained in the Remarks section of the present Response.